

REMARKS

Claims 1-25 are pending in the present application. Claims 1-7, 20, 22 and 24 are withdrawn from consideration. Claims 8-19, 21, 23, 25 are rejected. Claim 16 is herein canceled. Claim 8 is herein amended. New claim 26 is herein entered. No new matter has been entered.

Claim Rejections - 35 U.S.C. §102(b)

Claims 8, 16-17, 19 are rejected under 35 U.S.C. §102(b) as being anticipated by Moore (U.S. Patent Application Publication No. 2002/0111039 A1).

Applicants note that Moore teaches a method for depositing a silicon oxynitride (i.e. SiON) (paragraphs 0022-0031). In one embodiment of Moore, carbon is incorporated into the oxynitride film (i.e., SiOCN is formed - see paragraph 0028). In Moore, BTBAS is used as a raw material of silicon, and ammonia (NH₃), nitrous oxide (N₂O), nitric oxide (NO) or nitrogen (N₂) is used as a raw material of nitrogen (see paragraphs 0024-0025).

Applicants herein amend claim 8 to remove reference to SiON. Thereafter, Applicants submit that claims 8, 16-17, 19 are no longer subject to rejection under 35 U.S.C. §102(b) as anticipated by Moore because SiOCN is deleted from claim 8. Applicants note that Moore neither discloses nor suggests a method for fabricating a semiconductor device comprising the step of forming an insulation film of SiN or SiCN.

Claim Rejections - 35 U.S.C. §103

Claims 8-11, 15, 17-19, 21 are rejected under 35 U.S.C. §103(a) as being unpatentable over Arghavani et al. (U.S. Patent Application Publication No. U.S. 2004/0033677 A1) in view of Luo et al. (U.S. Patent Application Publication No. U.S. 2003/0059535 A1).

Claim 12 is rejected under 35 U.S.C. §103(a) as being unpatentable over Arghavani et al. and Luo et al., and further in view of Moore.

Claims 8, 17-19 are rejected under 35 U.S.C. §103(a) as being unpatentable over Xia et al. (U.S. Patent No. 6,153,261) in view of Luo et al.

Claims 13-14 are rejected under 35 U.S.C. §103(a) as being unpatentable over Xia et al. and Luo et al., and further in view of Huang et al. (U.S. Patent No. 6,077,769).

Claim 23 is rejected under 35 U.S.C. §103(a) as being unpatentable over Arghavani et al. and Luo et al., and further in view of Lee et al. (U.S. Patent Application Publication No. U.S. 2002/0151145 A1).

Claim 25 is rejected under 35 U.S.C. §103(a) as being unpatentable over Arghavani et al. and Luo et al., and further in view of Chatterjee (U.S. Patent Application Publication No. U.S. 2003/0102512 A1).

Applicants herein amend claim 8 as described above. Thereafter, Applicants submit that claims 8-15, 17-19, 21, 23, 25 are allowable because SiOCN is no longer read upon by claim 8, and claim 8 contains all of the features of claim 16 which is not rejected under 35 U.S.C. §103(a).

Applicants note that the present invention is characterized in that an insulation film of SiN or SiCN is formed by using a first raw material of a compound containing silicon and nitrogen, a second raw material of a compound containing a plurality of nitrogen atoms in a molecule and an additional third material of NH₃. In the present invention, since the additional third material of NH₃ is used, a leak current of the insulation film can be reduced. The cited references neither disclose nor suggest such feature or limitation of the present invention.

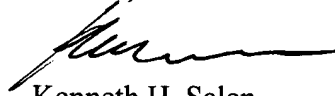
In view of the aforementioned amendments and accompanying remarks, Applicants submit that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney to arrange for an interview to expedite the disposition of this case.

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,

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